

50 V, 180 mA P-channel Trench MOSFET Rev. 1 — 23 May 2011

Product data sheet

Product profile 1.

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- ESD protection up to 1 kV
- AEC-Q101 qualified
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage	$T_j = 25 \ ^{\circ}C$	-	-	-50	V
gate-source voltage		-20	-	20	V
drain current	$V_{GS} = -10 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}$ [1]	-	-	-180	mA
racteristics					
drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = -10 \ V; I_D = -100 \ mA; \\ T_j = 25 \ ^\circ C \end{array}$	-	4.5	7.5	Ω
	drain-source voltage gate-source voltage drain current racteristics drain-source on-state	$\begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \textbf{V}_{GS} = -10 \text{ V}; \text{T}_{amb} = 25 ^\circ \text{C} \end{array} \begin{array}{c} \text{[1]} \\ \text{racteristics} \\ \\ \text{drain-source on-state} \\ \end{array} \\ \begin{array}{c} \text{V}_{GS} = -10 \text{ V}; \text{I}_{D} = -100 \text{ mA}; \end{array}$	$\begin{array}{c} \mbox{drain-source voltage} & T_{j} = 25 \ ^{\circ}\ C & - \\ \mbox{gate-source voltage} & & -20 \\ \mbox{drain current} & V_{GS} = -10 \ V; \ T_{amb} = 25 \ ^{\circ}\ C & \ \hline 1 \\ \mbox{racteristics} & & \\ \mbox{drain-source on-state} & V_{GS} = -10 \ V; \ I_{D} = -100 \ mA; & - \end{array}$	$\begin{array}{c} \text{drain-source voltage} \\ \text{drain-source voltage} \\ \text{drain current} \\ \text{drain current} \\ \text{drain-source on-state} \\ \end{array} \begin{array}{c} T_{j} = 25 \ ^{\circ}\text{C} \\ \text{-} \\ \text$	$\begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \text{drain source on-state} \\ \end{array} \begin{array}{c} T_{j} = 25 \ ^{\circ}\text{C} \\ -20 \\ \text{-20} \\ -20 \\ $

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source		
3	D	drain	1 ☐ ☐ 2 SOT23 (TO-236AB)	G Sym146

3. Ordering information

Table 3.	Ordering in	formation		
Type numb	ber	Package		
		Name	Description	Version
BSS84AK		TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
BSS84AK	%VS

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

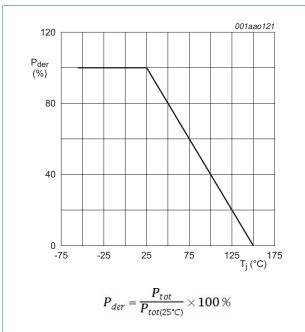
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-50	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = -10 V; T_{amb} = 25 °C	<u>[1]</u>	-	-180	mA
		$V_{GS} = -10 \text{ V}; \text{ T}_{amb} = 100 \text{ °C}$	<u>[1]</u>	-	-120	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-0.7	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	350	mW
			[1]	-	420	mW
		T _{sp} = 25 °C		-	1140	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-180	mA
ESD maxim	um rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	1000	V

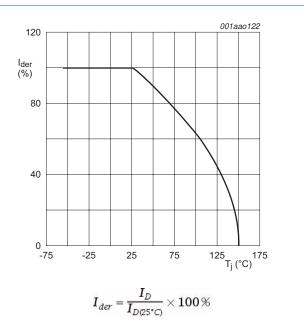
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



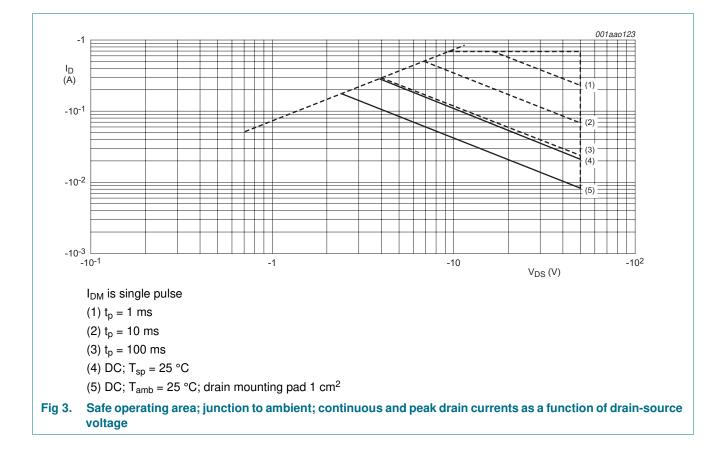






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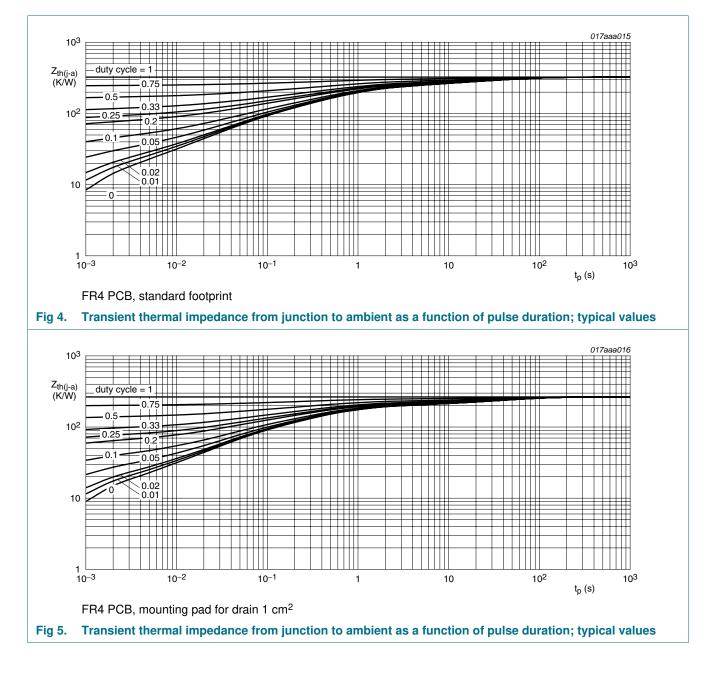


6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	310	370	K/W
			[2] _	260	300	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	115	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

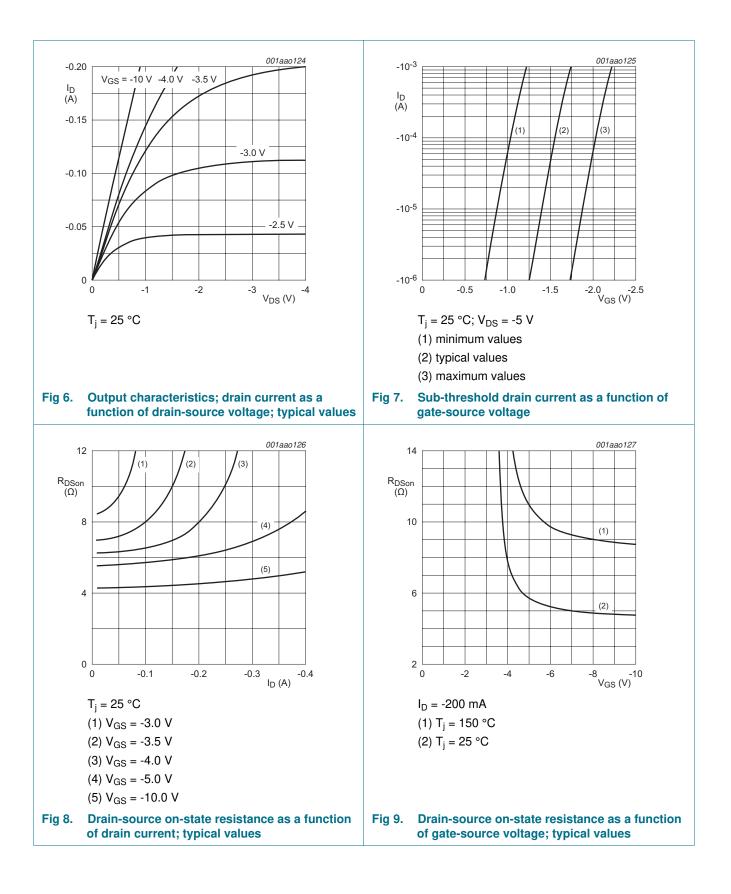


7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -10 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	-50	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; V_{DS} = V_{GS}; T_j = 25 \ ^\circ C$	-1.1	-1.6	-2.1	V
I _{DSS}	drain leakage current	$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-2	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I _D = -100 mA; T _j = 25 °C	-	4.5	7.5	Ω
	resistance	V_{GS} = -10 V; I _D = -100 mA; T _j = 150 °C	-	8	13.5	Ω
		$V_{GS} = -5 \text{ V}; \text{ I}_{D} = -100 \text{ mA}; \text{ T}_{j} = 25 \text{ °C}$	-	5.7	8.5	Ω
g _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -100 mA; T_j = 25 °C	-	150	-	mS
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -25 V; I _D = -200 mA; V _{GS} = -5 V;	-	0.26	0.35	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q _{GD}	gate-drain charge		-	0.09	-	nC
C _{iss}	input capacitance	V_{DS} = -25 V; f = 1 MHz; V_{GS} = 0 V;	-	24	36	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.5	-	pF
C _{rss}	reverse transfer capacitance		-	1.3	-	pF
t _{d(on)}	turn-on delay time	$V_{DS}=-30~V;~R_L=250~\Omega;~V_{GS}=-10~V;$	-	13	26	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}$	-	11	-	ns
t _{d(off)}	turn-off delay time		-	48	96	ns
t _f	fall time		-	25	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = -115 mA; V _{GS} = 0 V; T _i = 25 °C	-0.48	-0.85	-1.2	V

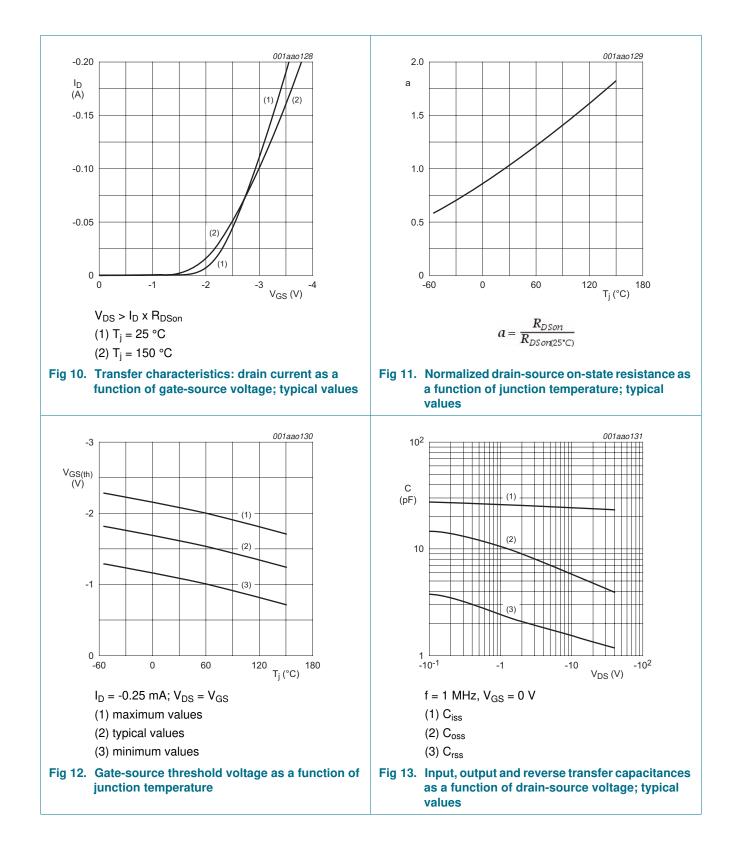
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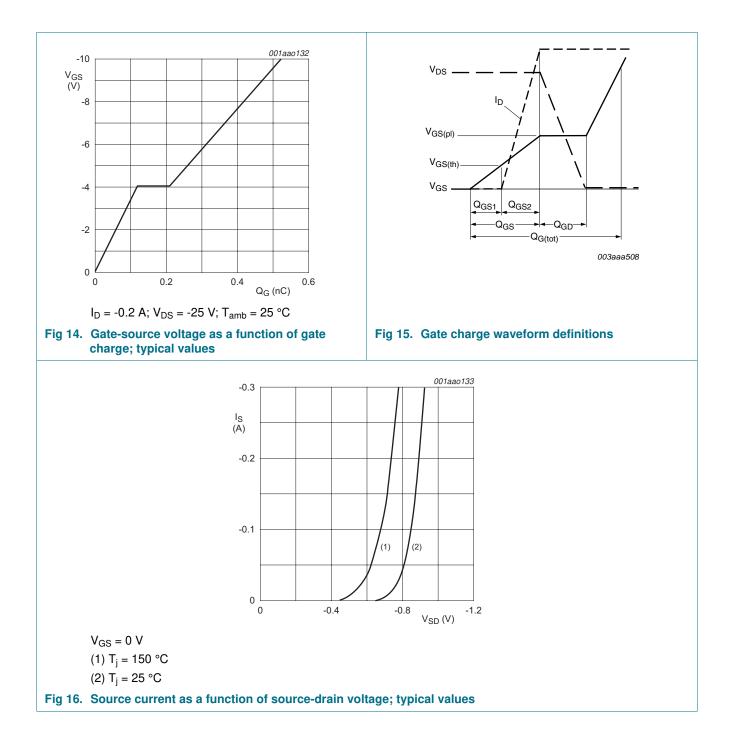
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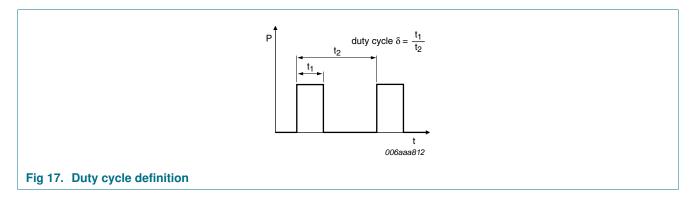


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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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9. Package outline

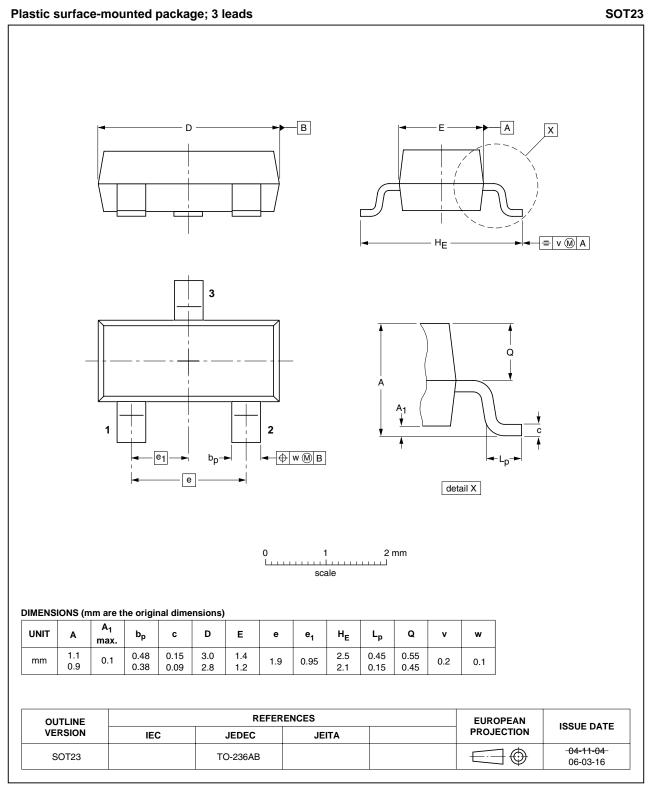
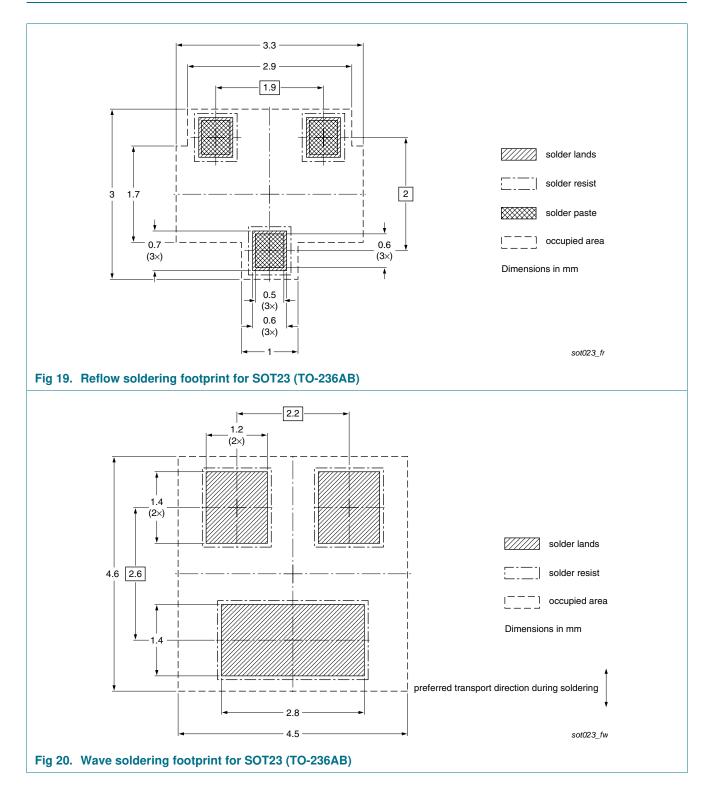


Fig 18. Package outline SOT23 (TO-236AB)

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10. Soldering



11. Revision history

Table 8.	Revision history						
Document	ID	Release date	Data sheet status	Change notice	Supersedes		
BSS84AK v	v.1	20110523	Product data sheet	-	-		

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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